

0.5 W Low-Cost Packaged PHEMT GaAs Power FETs

FEATURES

- 0.5 W Typical Output Power at 6 GHz
- 14 dB Typical Linear Power Gain at 6 GHz
- High Linearity: IP3 = 37 dBm Typical at 6 GHz
- High Power Added Efficiency:
Nominal PAE of 40 % at 6 GHz
- Suitable for High Reliability Application
- Breakdown Voltage: $BV_{DGO} \geq 15$ V
- $L_g = 0.35$ μ m, $W_g = 1.2$ mm
- Tight V_p ranges control
- High RF input power handling capability
- 100 % DC Tested
- Low Cost Ceramic Package

PHOTO ENLARGEMENT



DESCRIPTION

The TC2471 is packaged with the TC1401 Pseudomorphic High Electron Mobility Transistor (PHEMT) chip. The Cu-based ceramic package provides excellent thermal conductivity for the GaAs FET. All devices are 100% DC tested to assure consistent quality. Typical applications include high dynamic range power amplifiers for commercial and military high performance power applications.

ELECTRICAL SPECIFICATIONS ($T_A=25$ °C)

Symbol	CONDITIONS	MIN	TYP	MAX	UNIT
P_{1dB}	Output Power at 1dB Gain Compression Point, $f = 6$ GHz $V_{DS} = 8$ V, $I_{DS} = 120$ mA	26.5	27		dBm
G_L	Linear Power Gain, $f = 6$ GHz $V_{DS} = 8$ V, $I_{DS} = 120$ mA	12	14		dB
IP3	Intercept Point of the 3 rd -order Intermodulation, $f = 6$ GHz $V_{DS} = 8$ V, $I_{DS} = 120$ mA, $*P_{RCL} = 14$ dBm		37		dBm
PAE	Power Added Efficiency at 1dB Compression Power, $f = 6$ GHz		40		%
I_{DSS}	Saturated Drain-Source Current at $V_{DS} = 2$ V, $V_{GS} = 0$ V		300		mA
g_m	Transconductance at $V_{DS} = 2$ V, $V_{GS} = 0$ V		200		mS
V_p	Pinch-off Voltage at $V_{DS} = 2$ V, $I_D = 2.4$ mA		-1.7**		Volts
BV_{DGO}	Drain-Gate Breakdown Voltage at $I_{DGO} = 0.6$ mA	15	18		Volts
R_{th}	Thermal Resistance		30		°C/W

Note: * P_{SCL} : Output Power of Single Carrier Level

** For the tight control of the pinch-off voltage range, we divide TC2471 into 3 model numbers to fit customer design requirement

(1)TC2471P1519: $V_p = -1.5$ V to -1.9 V (2)TC2471P1620: $V_p = -1.6$ V to -2.0 V (3)TC2471P1721: $V_p = -1.7$ V to -2.1 V

If required, customer can specify the requirement in purchasing document. For special V_p requirement, please contact factory for details.

ABSOLUTE MAXIMUM RATINGS (T_A=25 ° C)

Symbol	Parameter	Rating
V _{DS}	Drain-Source Voltage	12 V
V _{GS}	Gate-Source Voltage	-5 V
I _{DS}	Drain Current	I _{DSS}
P _{in}	RF Input Power, CW	26 dBm
P _T	Continuous Dissipation	1.9 W
T _{CH}	Channel Temperature	175 °C
T _{STG}	Storage Temperature	- 65 °C to +175 °C

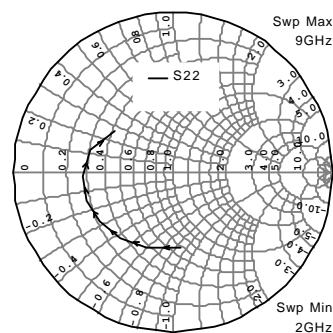
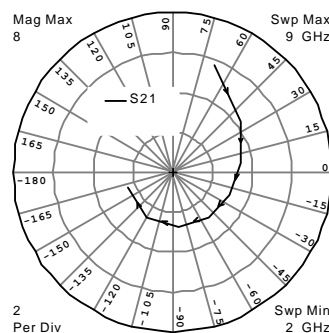
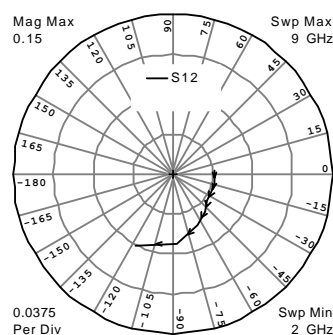
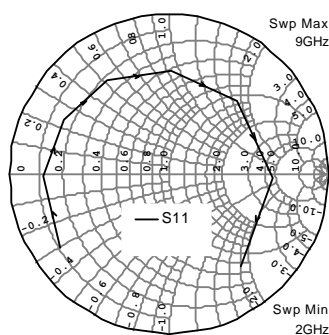
RECOMMENDED OPERATING CONDITION

Symbol	Parameter	Rating
V _{DS}	Drain to Source Voltage	8 V
I _D	Drain Current	120 mA

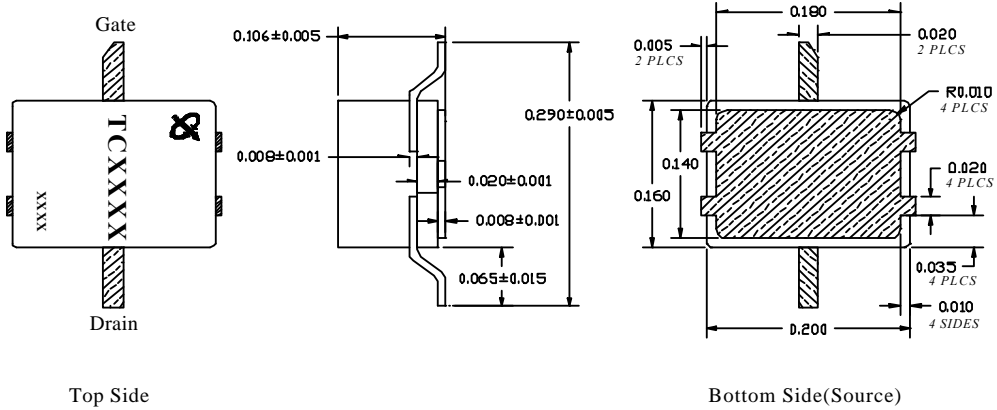
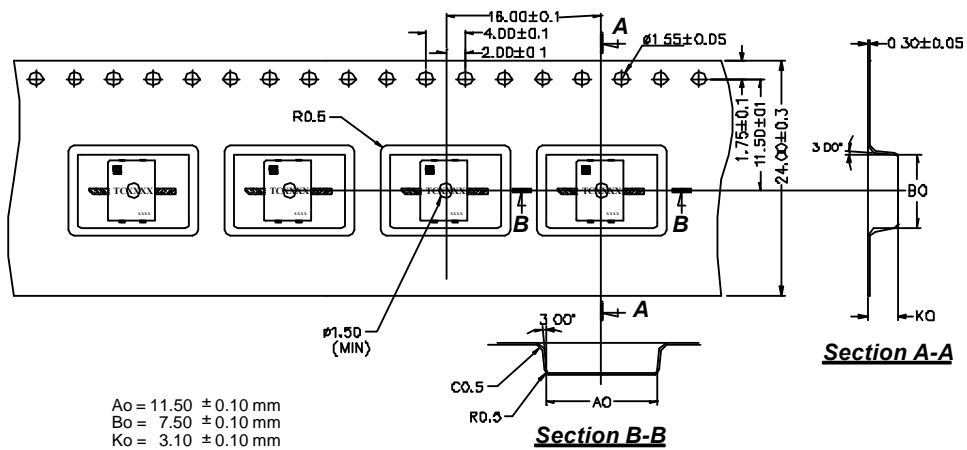
HANDLING PRECAUTIONS:

The user must operate in a clean, dry environment. Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. The static discharge must be less than 300V.

TYPICAL SCATTERING PARAMETERS (T_A=25 ° C)

 V_{DS} = 8 V, I_{DS} = 120 mA


FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2	0.8199	-145.81	5.7658	68.93	0.0387	4.89	0.4708	-84.58
3	0.7843	-179.36	4.2624	36.13	0.0399	-13.26	0.4977	-109.23
4	0.7452	152.75	3.4804	7.01	0.0403	-26.19	0.5295	-128.52
5	0.6992	123.46	3.0675	-21.51	0.0415	-38.13	0.5523	-145.68
6	0.6519	88.70	2.8445	-51.64	0.0462	-48.77	0.5654	-161.74
7	0.6272	46.67	2.7416	-84.42	0.0538	-63.69	0.5626	-177.61
8	0.6475	-1.92	2.6175	-120.45	0.0652	-86.78	0.5367	164.94
9	0.7296	-52.48	2.3753	-161.03	0.0752	-117.25	0.4441	144.53

OUTLINE DIMENSIONS (Unit: inch)

TAPE & REEL PACKAGE ORIENTATION (Unit: mm)


Standard Reel Size	7 ³⁵
Standard Reel Quantity	400